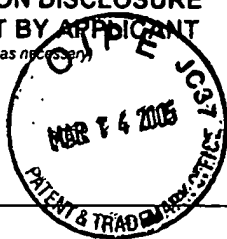


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First Named Inventor	Ahn, Kie
Group Art Unit	2829
Examiner Name	Sarkar, Asok

Sheet 1 of 1

Attorney Docket No: 1303.107US1

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Asok Kumar Sarkar

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